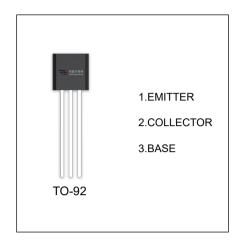


2SA1015 TRANSISTOR (PNP)

FEATURES

Power dissipation



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
2SA1015	TO-92	Bulk	1000pcs/Bag
2SA1015-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-150	mA
P _D	Collector Power Dissipation	400	mW
R ₀ JA	Thermal Resistance rom Junction to Ambient	312	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



$T_a \text{=} 25\,^\circ\!\!\subset\,$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -0.1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -50V,I _E =0			-0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} = -50V, I _B =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} = -6V, I _C = -2mA	70		700	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -100mA, I _B = -10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -100mA, I _B = -10mA			-1.1	V
Transition frequency	f _T	V _{CE} = -10 V, I _C = -1mA f =30MHz	80			MHz
Collector output capacitance	Cob	V _{CB} =-10V,I _E =0,f=1MH.			7	pF
Noise figure	NF	V _{CE} = -6 V, I _C = -0.1mA, f = 1#Hz,R _G =10#/			6	dB

CLASSIFICATION OF h_{FE}

Rank	0	Y	GR	BL
Range	70-140	120-240	200-400	350-700



